

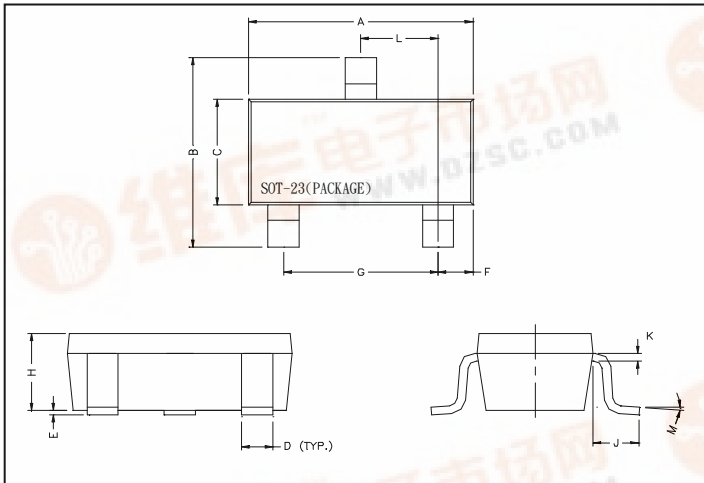
GBAV152

SURFACE MOUNT, SWITCHING DIODE VOLTAGE 80V, CURRENT 0.1A

Description

The GBAV152 is designed for ultra high speed switching application.

Package Dimensions



Marking:

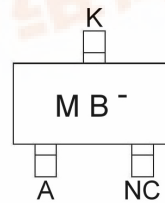
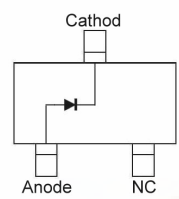


Diagram:



| REF. | Millimeter | | REF. | Millimeter | |
|------|------------|------|------|------------|------|
| | Min. | Max. | | Min. | Max. |
| A | 2.70 | 3.10 | G | 1.90 | REF. |
| B | 2.40 | 2.80 | H | 1.00 | 1.30 |
| C | 1.40 | 1.60 | K | 0.10 | 0.20 |
| D | 0.35 | 0.50 | J | 0.40 | - |
| E | 0 | 0.10 | L | 0.85 | 1.15 |
| F | 0.45 | 0.55 | M | 0 | 10° |

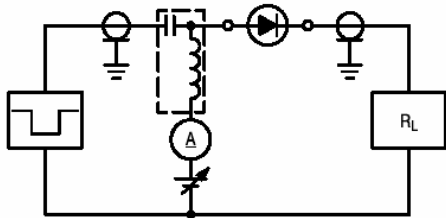
Absolute Maximum Ratings (At TA = 25°C unless otherwise specified)

| Parameter | Symbol | Ratings | Unit |
|--|-----------|------------|------|
| Max. Peak Reverse Voltage | V_{RM} | 80 | V |
| Max. Reverse Voltage | V_R | 80 | V |
| Max. Average Forward Rectified Current | I_o | 100 | mA |
| Non-Repetitive Peak Forward surge Current @ $T_p = 1.0\mu s$ @ $T_p = 1.0s$ | I_{FSM} | 225 | mA |
| | | 500 | |
| Power Dissipation | PD | 225 | mW |
| Junction Temperature | T_J | 150 | °C |
| Storage Temperature | T_{STG} | -55 ~ +150 | °C |

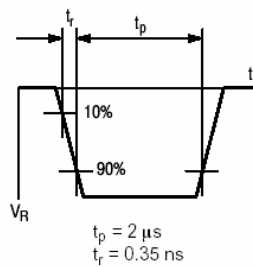
Electrical Characteristics (At TA = 25°C unless otherwise noted)

| Characteristics | Symbol | Min. | Max. | Unit | Test Conditions |
|----------------------------------|-------------|------|------|------|--|
| Reverse Breakdown Voltage | $V_{(BR)R}$ | 80 | - | V | $I_R = 100\mu A$ |
| Forward Voltage | V_F | - | 1.2 | V | $I_F = 100mA$ |
| Reverse Voltage Leakage Current | I_R | - | 100 | nA | $V_R = 75V$ |
| Diode Capacitance | C_D | - | 2.0 | pF | $V_R = 0V, f = 1.0MHz$ |
| Reverse Recovery Time (Figure 1) | t_{rr} | - | 3.0 | ns | $I_F = 10mA, V_R = 6V, R_L = 100\Omega, I_{rr} = 0.1I_R$ |

RECOVERY TIME EQUIVALENT TEST CIRCUIT



INPUT PULSE



OUTPUT PULSE

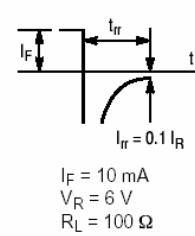


Figure 1. Reverse Recovery Time Equivalent Test Circuit

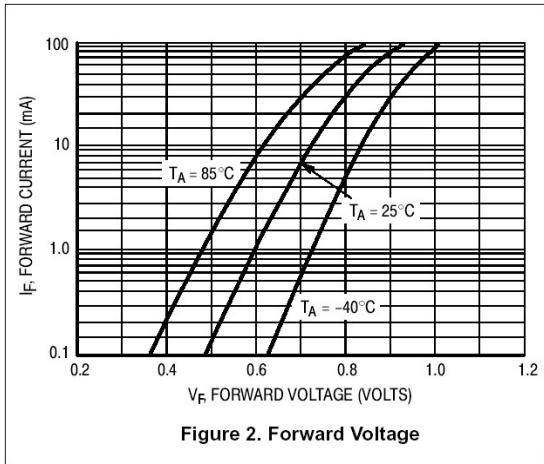


Figure 2. Forward Voltage

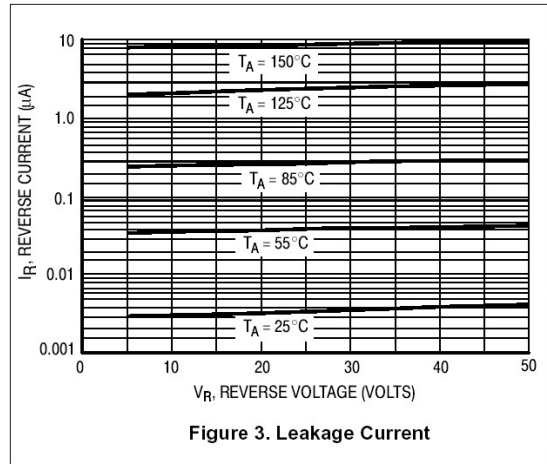


Figure 3. Leakage Current

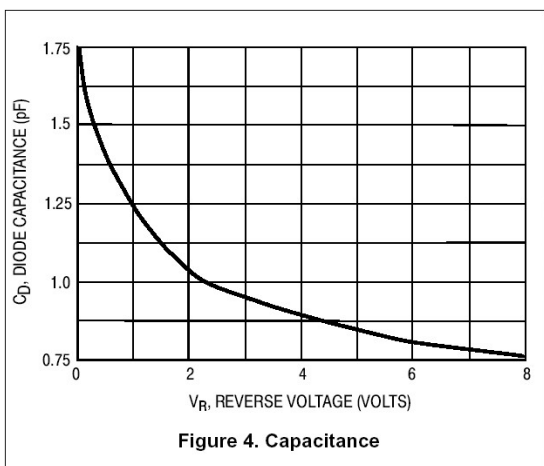


Figure 4. Capacitance

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